

# **Description**

The AO3407-HXY uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.



#### **General Features**

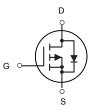
 $V_{DS} = -30V, I_{D} = -4.1A$ 

 $R_{DS(ON)}$  <56m $\Omega$  @  $V_{GS}$ =10V

# **SOT-23**

## **Application**

High power and current handing capability
Lead free product is acquired
Surface mount package
PWM applications
Load switch
Power management



P-Channel MOSFET

# **Package Marking and Ordering Information**

Product ID	Pack	Marking	Qty(PCS)
AO3407-HXY	SOT-23	3407	3000PCS

## Absolute Maximum Ratings (T<sub>A</sub>=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
VDS	Drain-Source Voltage	-30	V	
V <sub>G</sub> s	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Drain Current-Continuous	-4.1	Α	
Ірм	Drain Current-Pulsed (Note 1)	-13	Α	
P <sub>D</sub>	Maximum Power Dissipation	1.32	W	
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$	
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	125	°C/W	



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-30			V
△BV <sub>DSS</sub> /△T <sub>J</sub>	BVDSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA		-0.02		V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V , I <sub>D</sub> =-3A		48	56	mΩ
	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1.5A		78	90	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> . I <sub>D</sub> =-250uA	-1.2	-1.5	-2.5	V
$\triangle V_{GS(th)}$	GS(th)Temperature Coefficient	VGS-VDS , ID250UA		4.32		mV/°C
l	Drain Source Leakage Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C			-1	
IDSS	Drain-Source Leakage Current	V <sub>DS</sub> =-24V , V <sub>GS</sub> =0V , T <sub>J</sub> =55°C			-5	uA
Igss	Gate-Source Leakage Current	V <sub>GS</sub> =±20V , V <sub>DS</sub> =0V			±100	nA
gfs	Forward Transconductance	V <sub>DS</sub> =-5V , I <sub>D</sub> =-3A		4.8		S
Rg	Gate Resistance	V <sub>DS</sub> =0V , V <sub>GS</sub> =0V , f=1MHz		24	48	Ω
Qg	Total Gate Charge (-4.5V)			5.22	7.3	
Qgs	Gate-Source Charge	V <sub>DS</sub> =-20V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-3A		1.25	1.8	nC
$Q_{gd}$	Gate-Drain Charge			2.3	3.2	
T <sub>d(on)</sub>	Turn-On Delay Time			18.4	37	
Tr	Rise Time	$V_{DD}$ =-15V , $V_{GS}$ =-10V , $R_{G}$ =3.3 $\Omega$		11.4	21	
T <sub>d(off)</sub>	Turn-Off Delay Time	I <sub>D</sub> =-1A		39.4	79	ns
Tf	Fall Time			5.2	10.4	]
C <sub>iss</sub>	Input Capacitance			463	650	
Coss	Output Capacitance	V <sub>DS</sub> =-15V , V <sub>GS</sub> =0V , f=1MHz		82	115	pF
Crss	Reverse Transfer Capacitance			68	95	

#### **Diode Characteristics**

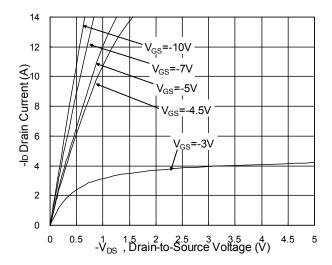
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current <sup>1,4</sup>	\\-=\\-=0\\			-3.2	Α
Ism	Pulsed Source Current <sup>2,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current			-13	Α
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C			-1	V

#### Note:

- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\,\leq\,300\text{us}$  , duty cycle  $\,\leq\,2\%$
- 3. The power dissipation is limited by 150°C junction temperature
- 4. The data is theoretically the same as  $I_D$  and  $I_{DM}$ , in real applications, should be limited by total power dissipation.



## **Typical Characteristics**



**Fig.1 Typical Output Characteristics** 

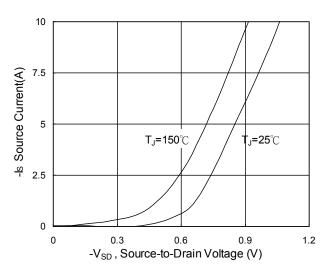


Fig.3 Source Drain Forward Characteristics

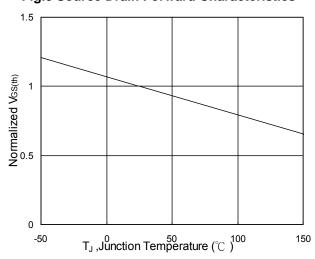


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

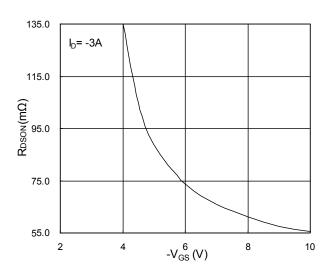


Fig.2 On-Resistance vs. G-S Voltage

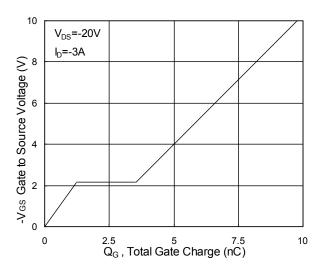


Fig.4 Gate-Charge Characteristics

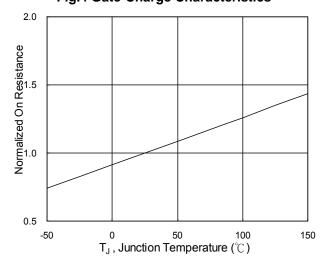
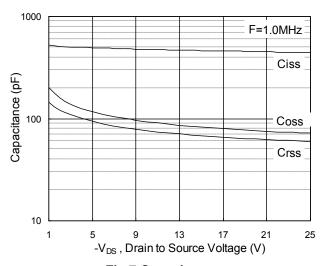


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





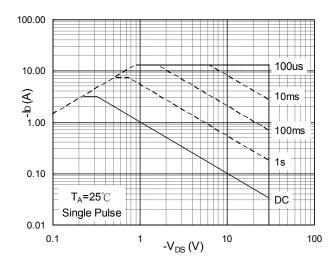


Fig.7 Capacitance

Fig.8 Safe Operating Area

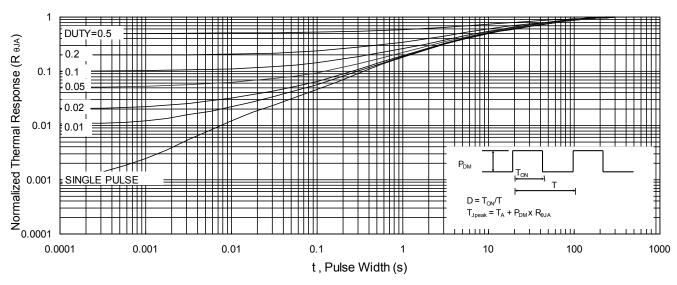
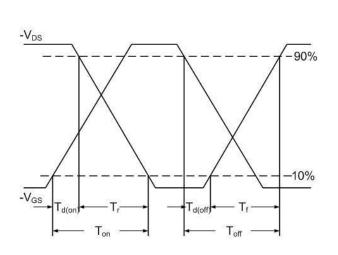


Fig.9 Normalized Maximum Transient Thermal Impedance



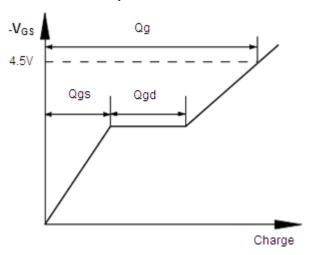
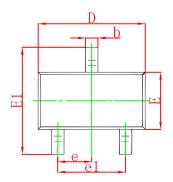


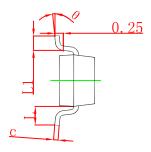
Fig.10 Switching Time Waveform

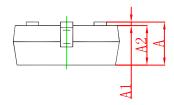
Fig.11 Gate Charge Waveform



# **SOT-23 Package Outline Dimensions**

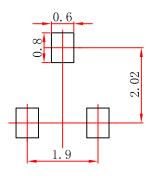






Cymphol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

# **SOT-23 Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
  3.The pad layout is for reference purposes only.



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